

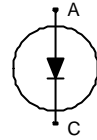
## Fast switching diode chip in EMCON 3-Technology

### FEATURES:

- 600V EMCON 3 technology 70  $\mu\text{m}$  chip
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient

### This chip is used for:

- power module



### Applications:

- drives

| Chip Type   | $V_R$ | $I_F$ | Die Size                   | Package      |
|-------------|-------|-------|----------------------------|--------------|
| SIDC50D60C6 | 600V  | 200A  | 9.2 x 5.44 mm <sup>2</sup> | sawn on foil |

### MECHANICAL PARAMETER:

|                                 |  |                 |
|---------------------------------|--|-----------------|
| Raster size                     | 9.2 x 5.44   | mm <sup>2</sup> |
| Area total / active             | 50.05 / 44.47  |                 |
| Anode pad size                  | 8.52 x 4.74  |                 |
| Thickness                       | 70   | $\mu\text{m}$   |
| Wafer size                      | 150  | mm              |
| Flat position                   | 180  | deg             |
| Max. possible chips per wafer   | 282 pcs  |                 |
| Passivation frontside           | Photoimide   |                 |
| Anode metallization             | 3200 nm AlSiCu   |                 |
| Cathode metallization           | Ni Ag –system<br>suitable for epoxy and soft solder die bonding                              |                 |
| Die bond                        | electrically conductive glue or solder   |                 |
| Wire bond                       | Al, $\leq 500\mu\text{m}$  |                 |
| Reject ink dot size             | $\varnothing$ 0.65mm; max 1.2mm  |                 |
| Recommended storage environment | store in original container, in dry nitrogen,<br>< 6 month at an ambient temperature of 23°C |                 |

## Maximum Ratings

| Parameter  | Symbol         | Condition | Value      | Unit |
|--|----------------|-----------|------------|------|
| Repetitive peak reverse voltage                          | $V_{RRM}$      |           | 600        | V    |
| Continuous forward current limited by $T_{jmax}$         | $I_F$          |           | 1)         | A    |
| Maximum repetitive forward current limited by $T_{jmax}$ | $I_{FRM}$      |           | 400        |      |
| Operating junction and storage temperature               | $T_j, T_{stg}$ |           | -40...+175 | °C   |

1) depending on thermal properties of assembly

Static Electrical Characteristics (tested on chip),  $T_j=25\text{ °C}$ , unless otherwise specified

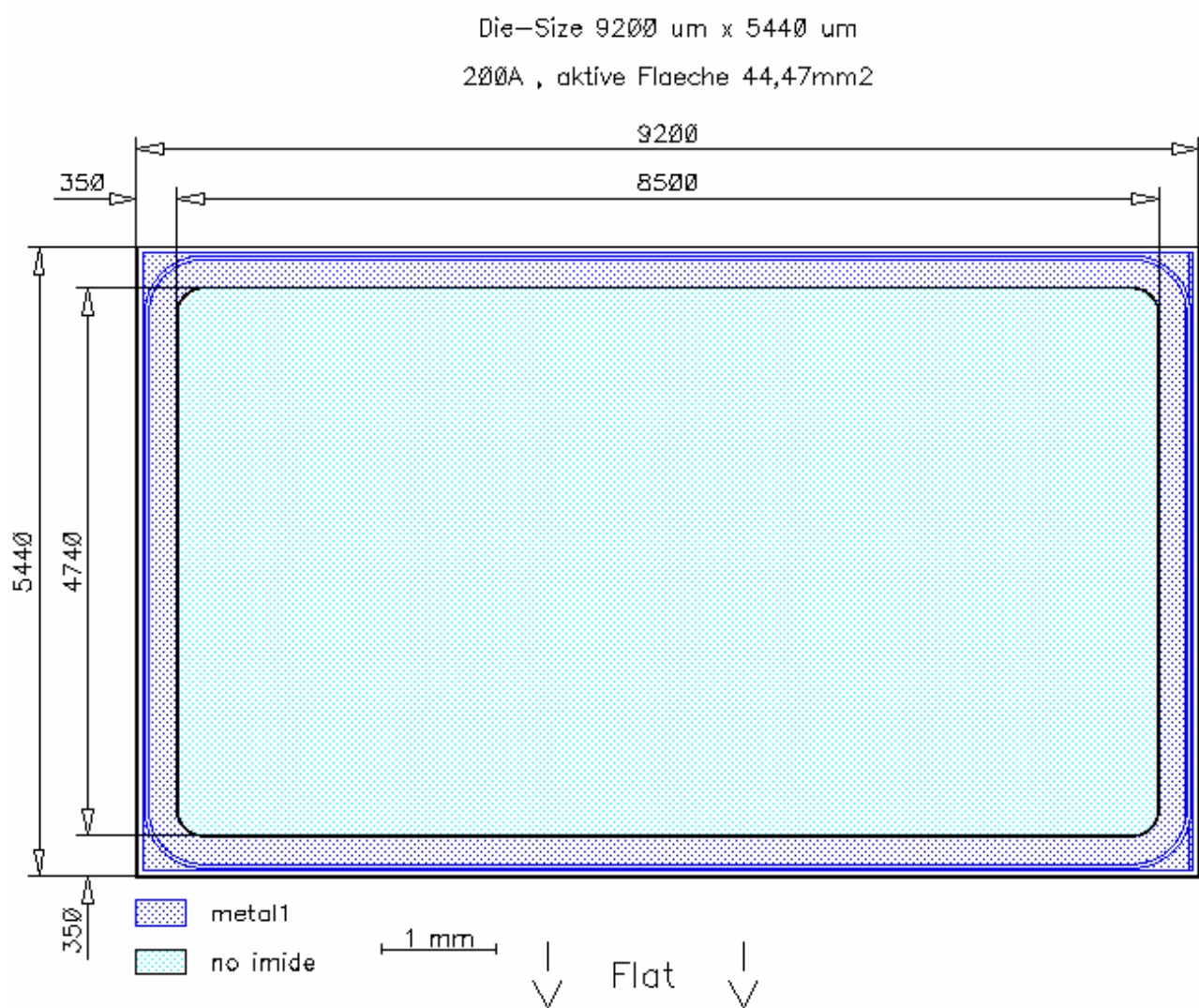
| Parameter                       | Symbol   | Conditions   |                    | Value |      |      | Unit |
|---------------------------------|----------|--------------|--------------------|-------|------|------|------|
|                                 |          |              |                    | min.  | Typ. | max. |      |
| Reverse leakage current         | $I_R$    | $V_R=600V$   | $T_j=25\text{ °C}$ |       |      | 27   | µA   |
| Cathode-Anode breakdown Voltage | $V_{Br}$ | $I_R=0.25mA$ | $T_j=25\text{ °C}$ | 600   |      |      | V    |
| Forward voltage drop            | $V_F$    | $I_F=200A$   | $T_j=25\text{ °C}$ | 1.2   | 1.6  | 1.9  | V    |

Dynamic Electrical Characteristics (verified by design/characterization), inductive load

| Parameter                     | Symbol    | Conditions  |  | Value <sup>2)</sup> |                      |      | Unit |
|-------------------------------|-----------|---|--|---------------------|----------------------|------|------|
|                               |           |   |  | min.                | Typ.                 | max. |      |
| Peak reverse recovery current | $I_{RM}$  | $I_F=200A$<br>$di/dt=5700A/ms$<br>$V_R=300V$<br>$V_{GE}=-15V$ | $T_j = 25\text{ °C}$<br>$T_j = 125\text{ °C}$<br>$T_j = 150\text{ °C}$ |                     | 160<br>230<br>240    |      | A    |
| Recovered charge              | $Q_r$     | $I_F=200A$<br>$di/dt=5700A/ms$<br>$V_R=300V$<br>$V_{GE}=-15V$ | $T_j = 25\text{ °C}$<br>$T_j = 125\text{ °C}$<br>$T_j = 150\text{ °C}$ |                     | 10.0<br>17.0<br>20.0 |      | µC   |
| Reverse recovery energy       | $E_{rec}$ | $I_F=200A$<br>$di/dt=5700A/ms$<br>$V_R=300V$<br>$V_{GE}=-15V$ | $T_j = 25\text{ °C}$<br>$T_j = 125\text{ °C}$<br>$T_j = 150\text{ °C}$ |                     | 3.00<br>5.20<br>5.80 |      | mJ   |

<sup>2)</sup> values also influenced by parasitic L- and C- in measurement and package.

## CHIP DRAWING:





# SIDC50D60C6

## FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the device data sheet

FS200R06KE3

### Description:

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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